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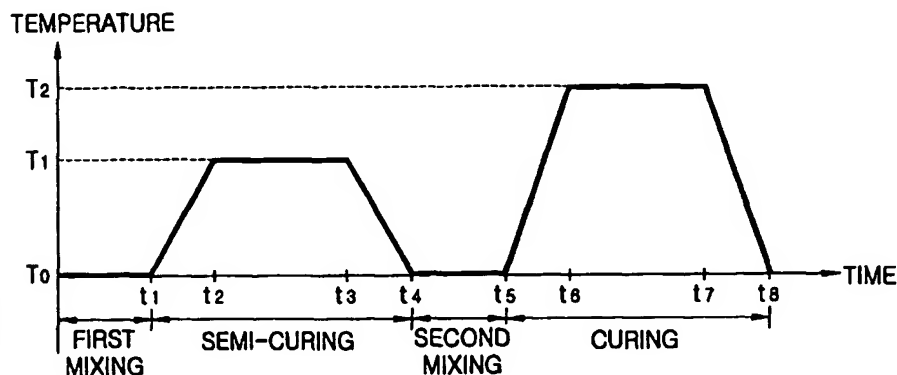
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(54) Title: MANUFACTURING METHOD FOR WHITE LIGHT EMITTING DIODE DEVICE INCLUDING TWO STEP CURE
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(57) Abstract: Provided is a method of manufacturing a light emitting diode (LED) device which has excellent optical properties. The method includes: mixing a main gradient with a curing agent at room temperature to obtain the liquid epoxy resin; semi-curing the liquid epoxy resin at 70-1000°C under 1-30 torr; adding a phosphor to the semi-cured liquid epoxy resin at room temperature and mixing the phosphor and the semi-cured liquid epoxy resin to obtain a

mother resin mixed with the phosphor; feeding the obtained product into an element to be molded comprising a LED chip; and completely curing the mother resin at 120°C or higher under an ambient pressure.

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